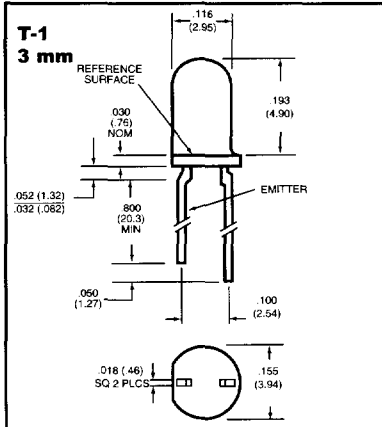
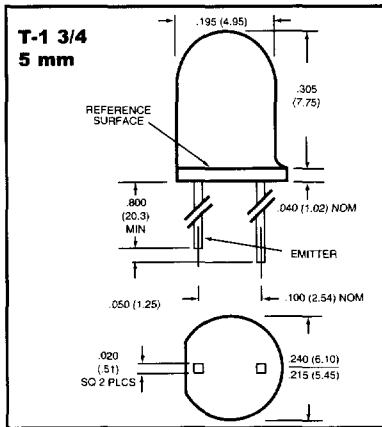


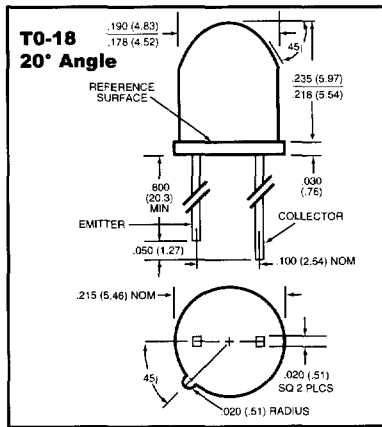
PLASTIC SILICON INFRARED PHOTSENSORS



Part Number	Reception Angle @		$I_{C(ON)}$		units	BV_{CEO} (V)	I_{CEO}/V_{CE} (nA)/(V)	Notes
	1/2 Sensitivity	min	max	min				
Phototransistor								
QSC112	$\pm 8^\circ$	1.00	4.00	mA	30	100/10	1	
QSC113	$\pm 8^\circ$	2.40	9.60	mA	30	100/10	1	
QSC114	$\pm 8^\circ$	4.00	-	mA	30	100/10	1	
Photodarlington								
QSC133	$\pm 8^\circ$	8.00	-	mA	30	100/10	3, 6, 7	

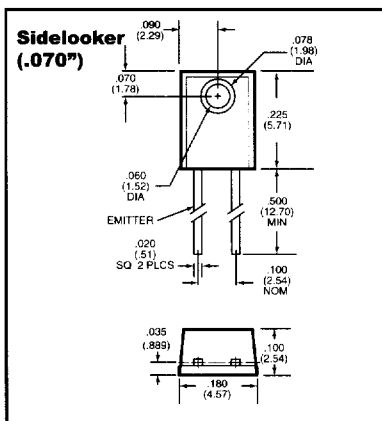


Part Number	Reception Angle @		$I_{C(ON)}$		units	BV_{CEO} (V)	I_{CEO}/V_{CE} (nA)/(V)	Notes
	1/2 Sensitivity	min	max	min				
Phototransistor								
QSD122	$\pm 12^\circ$	1.00	6.00	mA	30	100/10	1	
QSD123	$\pm 12^\circ$	4.00	16.0	mA	30	100/10	1	
QSD124	$\pm 12^\circ$	6.00	-	mA	30	100/10	1	
QSD128	$\pm 12^\circ$	6.00	-	mA	30	100/10	1, 6	

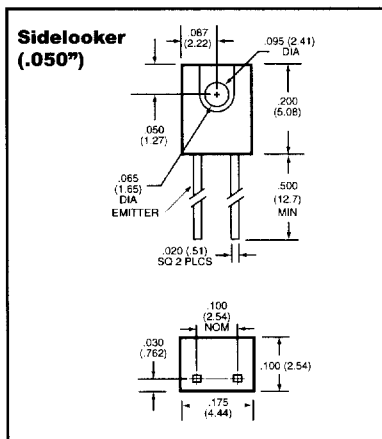


Part Number	Reception Angle @		$I_{C(ON)}$		units	BV_{CEO} (V)	I_{CEO}/V_{CE} (nA)/(V)	Notes
	1/2 Sensitivity	min	max	min				
Phototransistor								
QSD722	$\pm 20^\circ$	0.60	3.80	mA	30	100/10	1	
QSD723	$\pm 20^\circ$	2.50	10.0	mA	30	100/10	1	
QSD724	$\pm 20^\circ$	3.50	-	mA	30	100/10	1	
Photodarlington								
QSD733	$\pm 20^\circ$	5.00	-	mA	30	100/10	5, 7	

PLASTIC SILICON INFRARED PHOTSENSORS



Part Number	Reception		I _{C(ON)} min	I _{C(ON)} max	units	BV _{CEO} (V)		I _{CEO} /V _{CE} (nA)/(V)		Notes
	Angle @ 1/2 Sensitivity					min	max	min	max	
Phototransistor										
L14Q1 *	±35°		1.00	–	mA	30		100/25		4
Photodarlington										
L14R1 *	±35°		5.00	–	mA	30		100/25		2



Part Number	Reception		I _{C(ON)} min	I _{C(ON)} max	units	BV _{CEO} (V)		I _{CEO} /V _{CE} (nA)/(V)		Notes
	Angle @ 1/2 Sensitivity					min	max	min	max	
Phototransistor										
QSE113	±25°		0.25	1.50	mA	30		100/10		1
QSE114	±25°		1.00	–	mA	30		100/10		1
QSE122	±25°		3.00	12.0	mA	30		100/10		1
Photodarlington										
QSE133	±35°		9.00	–	mA	30		100/10		3

Notes (Applies to all components on pages 35 and 36.)

1. On-State Collector Current @ E_e = 0.5 mW/cm² (AlGaAs), V_{CE} = 5 V
2. On-State Collector Current @ E_e = 0.3 mW/cm² (GaAs), V_{CE} = 1.5 V
3. On-State Collector Current @ E_e = 0.25 mW/cm² (AlGaAs), V_{CE} = 5 V
4. On-State Collector Current @ E_e = 1.5 mW/cm² (GaAs), V_{CE} = 5 V
5. On-State Collector Current @ E_e = 0.125 mW/cm² (AlGaAs), V_{CE} = 5 V
6. Reverse Polarity
7. Orange stripe on the flange

Maximum Ratings Table B (Applies to all components on pages 35 and 36.)

Storage Temperature	-40 to +100° C
Operating Temperature	-40 to +100° C
Soldering:	
Lead Temperature (Iron)	240° C for 5 s
Lead Temperature (Flow)	260° C for 10 s
Collector-Emitter Breakdown Voltage	30 V
Emitter-Collector Breakdown Voltage	
(L14R, QSE133)	6.0 V
(QSX, L14Q)	5.0 V
Power Dissipation	150 mW
Derate linearly at 2.00 mW/° C above 25° C	